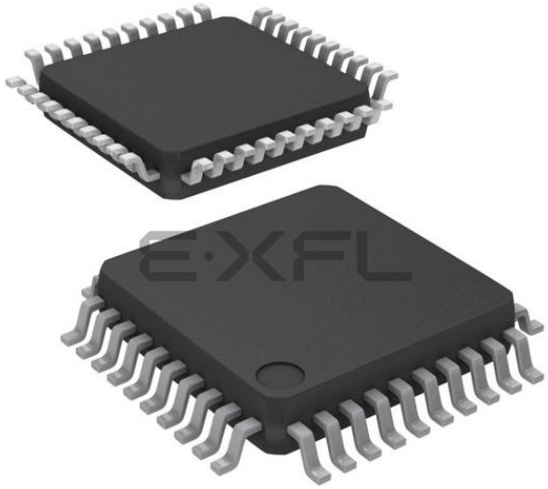
Renesas Electronics America Inc - R5F21334TNFP#50 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	27
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21334tnfp-50

1.2 Product List

Table 1.3 lists Product List for R8C/33T Group. Figure 1.1 shows a Part Number, Memory Size, and Package of R8C/33T Group.

Table 1.3 Product List for R8C/33T Group **Current of Apr 2011**

Part No.	ROM Capacity		RAM Capacity	Package Type	Remarks
	Program ROM	Data flash			
R5F21334TNFP	16 Kbytes	1 Kbyte × 4	1.5 Kbytes	PLQP0032GB-A	N version
R5F21335TNFP	24 Kbytes	1 Kbyte × 4	2 Kbytes	PLQP0032GB-A	
R5F21336TNFP	32 Kbytes	1 Kbyte × 4	2.5 Kbytes	PLQP0032GB-A	
R5F21334TNXXXFP	16 Kbytes	1 Kbyte × 4	1.5 Kbytes	PLQP0032GB-A	N version Factory-programming product (1)
R5F21335TNXXXFP	24 Kbytes	1 Kbyte × 4	2 Kbytes	PLQP0032GB-A	
R5F21336TNXXXFP	32 Kbytes	1 Kbyte × 4	2.5 Kbytes	PLQP0032GB-A	

Note:
1. The user ROM is programmed before shipment.

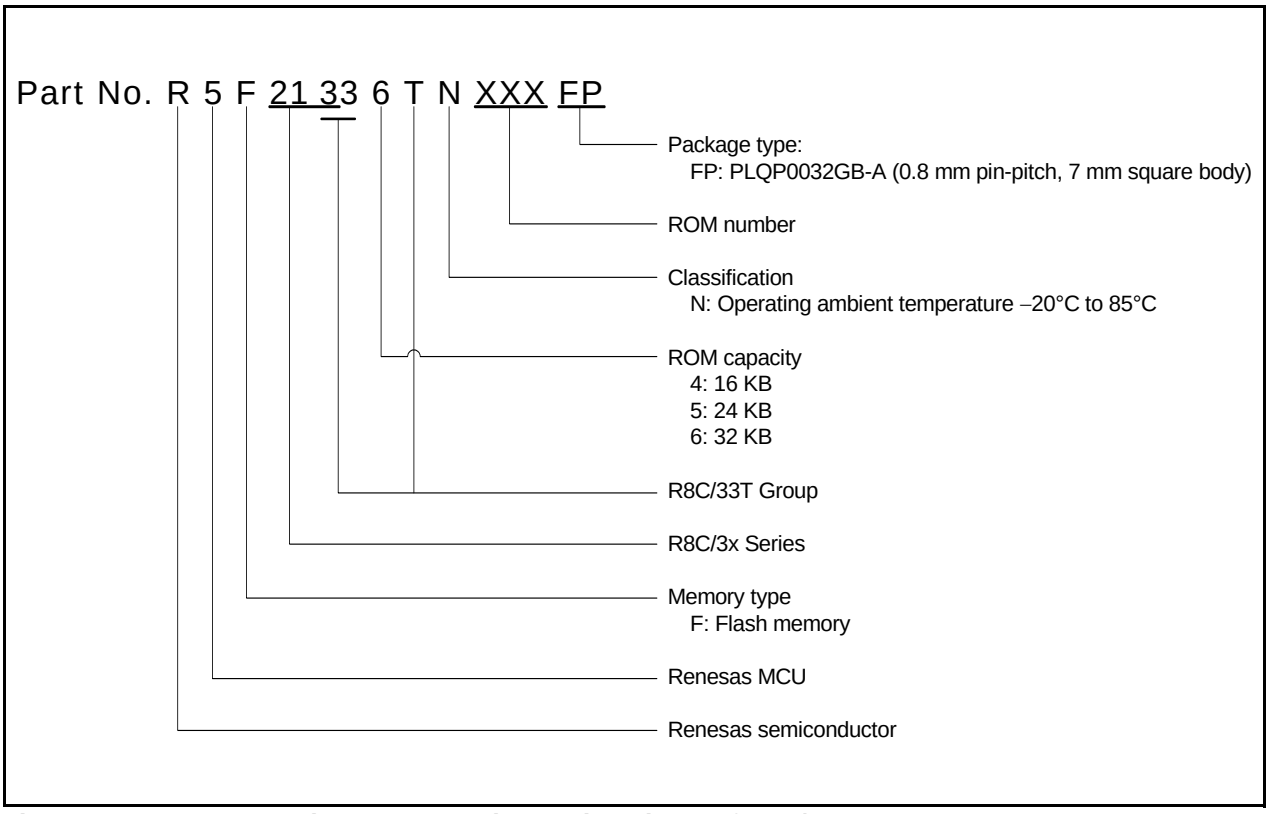


Figure 1.1 Part Number, Memory Size, and Package of R8C/33T Group

1.4 Pin Assignment

Figure 1.3 shows Pin Assignment (Top View). Table 1.4 outlines the Pin Name Information by Pin Number.

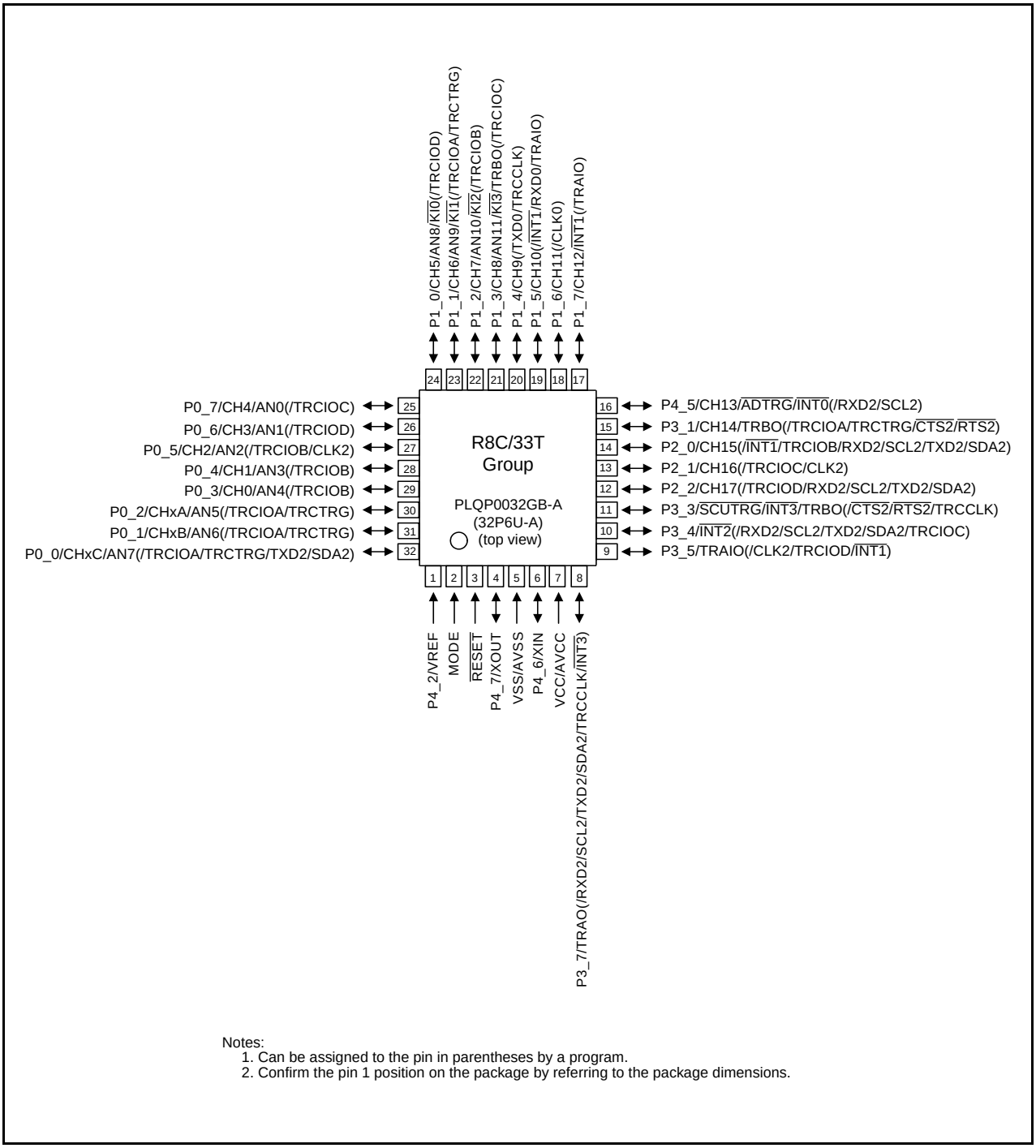
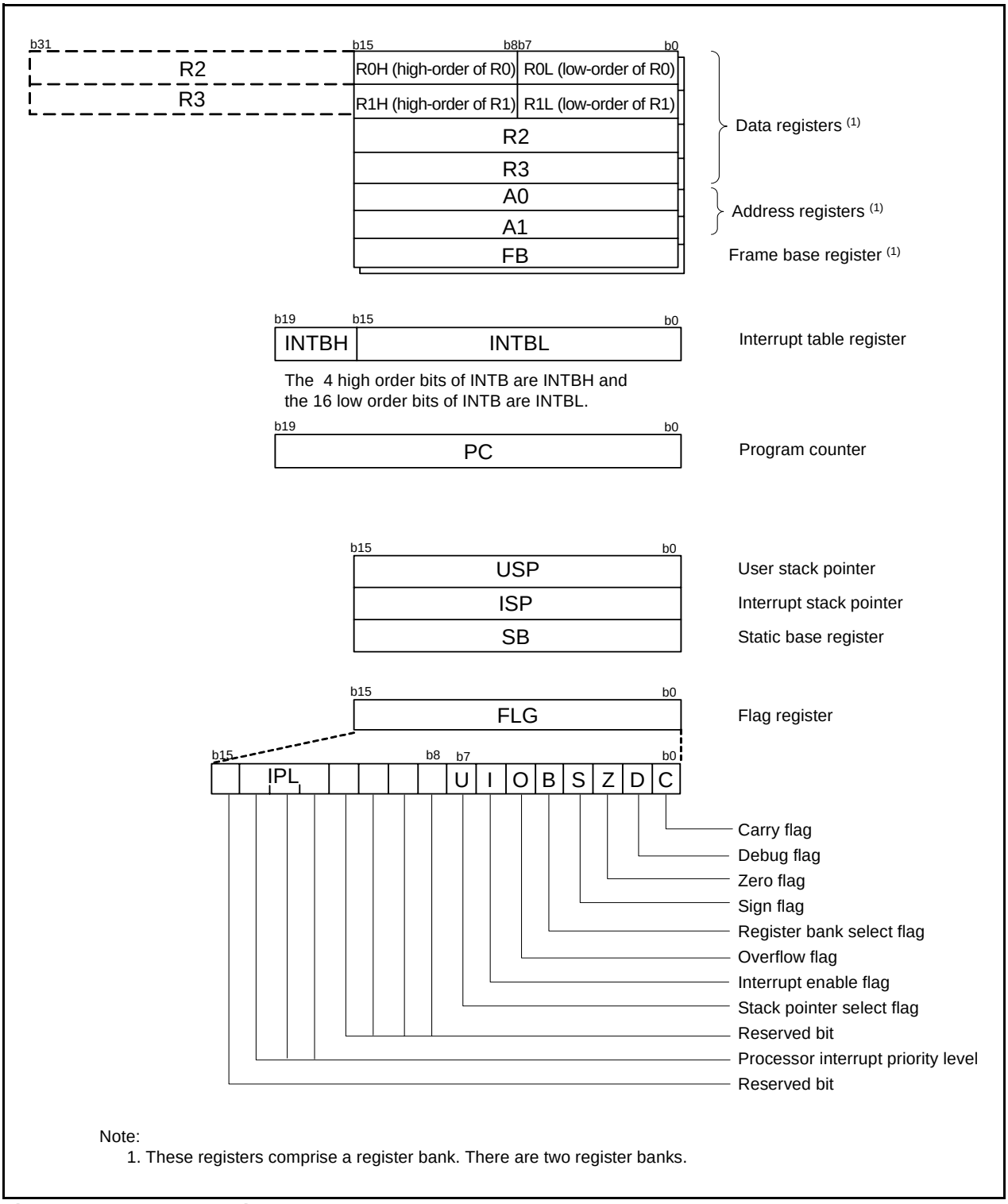


Figure 1.3 Pin Assignment (Top View)

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.



Note:
1. These registers comprise a register bank. There are two register banks.

Figure 2.1 CPU Registers

2.1 Data Registers (R0, R1, R2, and R3)

R0 is a 16-bit register for transfer, arithmetic, and logic operations. The same applies to R1 to R3. R0 can be split into high-order bits (R0H) and low-order bits (R0L) to be used separately as 8-bit data registers. R1H and R1L are analogous to R0H and R0L. R2 can be combined with R0 and used as a 32-bit data register (R2R0). R3R1 is analogous to R2R0.

2.2 Address Registers (A0 and A1)

A0 is a 16-bit register for address register indirect addressing and address register relative addressing. It is also used for transfer, arithmetic, and logic operations. A1 is analogous to A0. A1 can be combined with A0 and as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register that indicates the starting address of an interrupt vector table.

2.5 Program Counter (PC)

PC is 20 bits wide and indicates the address of the next instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The stack pointers (SP), USP and ISP, are each 16 bits wide. The U flag of FLG is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register for SB relative addressing.

2.8 Flag Register (FLG)

FLG is an 11-bit register indicating the CPU state.

2.8.1 Carry Flag (C)

The C flag retains carry, borrow, or shift-out bits that have been generated by the arithmetic and logic unit.

2.8.2 Debug Flag (D)

The D flag is for debugging only. Set it to 0.

2.8.3 Zero Flag (Z)

The Z flag is set to 1 when an arithmetic operation results in 0; otherwise to 0.

2.8.4 Sign Flag (S)

The S flag is set to 1 when an arithmetic operation results in a negative value; otherwise to 0.

2.8.5 Register Bank Select Flag (B)

Register bank 0 is selected when the B flag is 0. Register bank 1 is selected when this flag is set to 1.

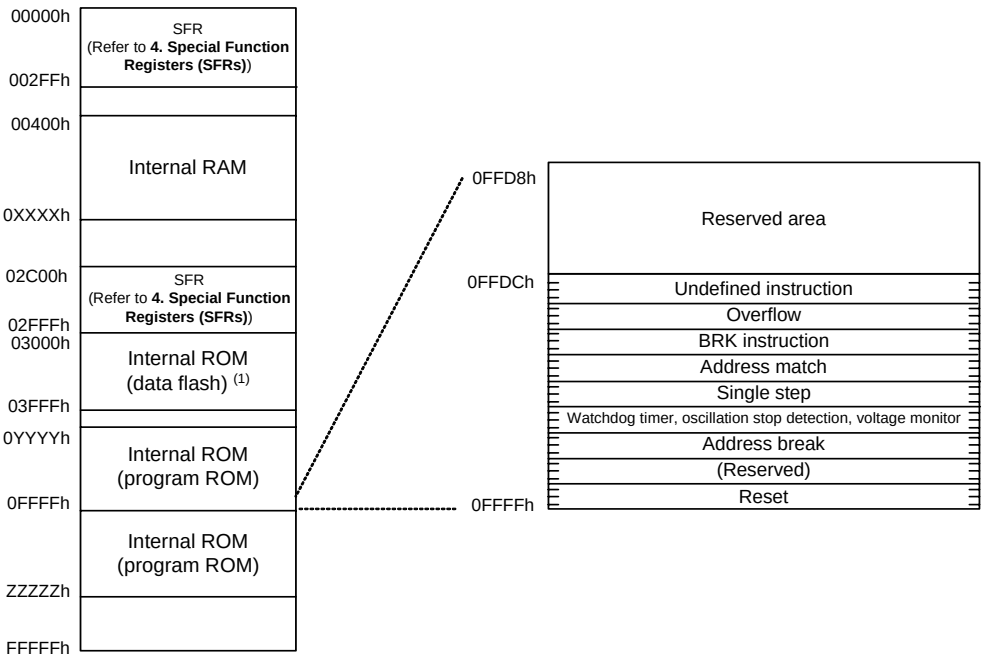
2.8.6 Overflow Flag (O)

The O flag is set to 1 when an operation results in an overflow; otherwise to 0.

3. Memory

3.1 R8C/33T Group

Figure 3.1 is a Memory Map of R8C/33T Group. The R8C/33T Group has a 1-Mbyte address space from addresses 00000h to FFFFFh. For example, a 32-Kbyte internal ROM area is allocated addresses 08000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. The starting address of each interrupt routine is stored here.
The internal ROM (data flash) is allocated addresses 03000h to 03FFFh.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM area is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for data storage but also as a stack area when a subroutine is called or when an interrupt request is acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh and 02C00h to 02FFFh. Peripheral function control registers are allocated here. All unallocated spaces within the SFRs are reserved and cannot be accessed by users.



Notes:
1. Data flash indicates block A (1 Kbyte), block B (1 Kbyte), block C (1 Kbyte), and block D (1 Kbyte).
2. The blank areas are reserved and cannot be accessed by users.

Part Number	Internal ROM			Internal RAM	
	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh
R5F21334TNFP, R5F21334TDFP, R5F21334TNXXXFP, R5F21334TDXXXFP	16 Kbytes	0C000h	—	1.5 Kbytes	009FFh
R5F21335TNFP, R5F21335TDFP, R5F21335TNXXXFP, R5F21335TDXXXFP	24 Kbytes	0A000h	—	2 Kbytes	00BFFh
R5F21336TNFP, R5F21336TDFP, R5F21336TNXXXFP, R5F21336TDXXXFP	32 Kbytes	08000h	—	2.5 Kbytes	00DFFh

Figure 3.1 Memory Map of R8C/33T Group

4. Special Function Registers (SFRs)

An SFR (special function register) is a control register for a peripheral function. Tables 4.1 to 4.12 list the special function registers. Table 4.13 lists the ID Code Areas and Option Function Select Area.

Table 4.1 SFR Information (1) [1]

Address	Register	Symbol	After Reset
0000h			
0001h			
0002h			
0003h			
0004h	Processor Mode Register 0	PM0	00h
0005h	Processor Mode Register 1	PM1	00h
0006h	System Clock Control Register 0	CM0	00101000b
0007h	System Clock Control Register 1	CM1	00100000b
0008h	Module Standby Control Register	MSTCR	00h
0009h	System Clock Control Register 3	CM3	00h
000Ah	Protect Register	PRCR	00h
000Bh	Reset Source Determination Register	RSTFR	0XXXXXXXb [2]
000Ch	Oscillation Stop Detection Register	OCD	00000100b
000Dh	Watchdog Timer Reset Register	WDTR	XXh
000Eh	Watchdog Timer Start Register	WDTS	XXh
000Fh	Watchdog Timer Control Register	WDTC	00111111b
0010h			
0011h			
0012h			
0013h			
0014h			
0015h	High-Speed On-Chip Oscillator Control Register 7	FRA7	When shipping
0016h			
0017h			
0018h			
0019h			
001Ah			
001Bh			
001Ch	Count Source Protection Mode Register	CSPR	00h 10000000b [3]
001Dh			
001Eh			
001Fh			
0020h			
0021h			
0022h			
0023h	High-Speed On-Chip Oscillator Control Register 0	FRA0	00h
0024h	High-Speed On-Chip Oscillator Control Register 1	FRA1	When shipping
0025h	High-Speed On-Chip Oscillator Control Register 2	FRA2	00h
0026h	On-Chip Reference Voltage Control Register	OCVREFCR	00h
0027h			
0028h	Clock Prescaler Reset Flag	CPSRF	00h
0029h	High-Speed On-Chip Oscillator Control Register 4	FRA4	When shipping
002Ah	High-Speed On-Chip Oscillator Control Register 5	FRA5	When shipping
002Bh	High-Speed On-Chip Oscillator Control Register 6	FRA6	When shipping
002Ch			
002Dh			
002Eh			
002Fh	High-Speed On-Chip Oscillator Control Register 3	FRA3	When shipping
0030h	Voltage Monitor Circuit Control Register	CMPA	00h
0031h	Voltage Monitor Circuit Edge Select Register	VCAC	00h
0032h			
0033h	Voltage Detect Register 1	VCA1	00001000b
0034h	Voltage Detect Register 2	VCA2	00h [4] 00100000b [5]
0035h			
0036h	Voltage Detection 1 Level Select Register	VD1LS	00000111b
0037h			
0038h	Voltage Monitor 0 Circuit Control Register	VW0C	1100X010b [4] 1100X011b [5]
0039h	Voltage Monitor 1 Circuit Control Register	VW1C	10001010b

X: Undefined

Notes:

1. The blank areas are reserved and cannot be accessed by users.
2. The CWR bit in the RSTFR register is set to 0 after power-on and voltage monitor 0 reset. Hardware reset, Software reset, or watchdog timer reset does not affect this bit.
3. The CSPROINI bit in the OFS register is set to 0.
4. The LVDAS bit in the OFS register is set to 1.
5. The LVDAS bit in the OFS register is set to 0.

Table 4.8 SFR Information (8) (1)

Address	Register	Symbol	After Reset
01C0h	Address Match Interrupt Register 0	RMAD0	XXh
01C1h			XXh
01C2h			0000XXXXb
01C3h	Address Match Interrupt Enable Register 0	AIER0	00h
01C4h	Address Match Interrupt Register 1	RMAD1	XXh
01C5h			XXh
01C6h			0000XXXXb
01C7h	Address Match Interrupt Enable Register 1	AIER1	00h
01C8h			
01C9h			
01CAh			
01CBh			
01CCh			
01CDh			
01CEh			
01CFh			
01D0h			
01D1h			
01D2h			
01D3h			
01D4h			
01D5h			
01D6h			
01D7h			
01D8h			
01D9h			
01DAh			
01DBh			
01DCh			
01DDh			
01DEh			
01DFh			
01E0h	Pull-Up Control Register 0	PUR0	00h
01E1h	Pull-Up Control Register 1	PUR1	00h
01E2h			
01E3h			
01E4h			
01E5h			
01E6h			
01E7h			
01E8h			
01E9h			
01EAh			
01EBh			
01ECh			
01EDh			
01EEh			
01EFh			
01F0h	Port P1 Drive Capacity Control Register	P1DRR	00h
01F1h	Port P2 Drive Capacity Control Register	P2DRR	00h
01F2h	Drive Capacity Control Register 0	DRR0	00h
01F3h	Drive Capacity Control Register 1	DRR1	00h
01F4h			
01F5h	Input Threshold Control Register 0	VLT0	00h
01F6h	Input Threshold Control Register 1	VLT1	00h
01F7h			
01F8h			
01F9h			
01FAh	External Input Enable Register 0	INTEN	00h
01FBh			
01FCh	INT Input Filter Select Register 0	INTF	00h
01FDh			
01FEh	Key Input Enable Register 0	KIEN	00h
01FFh			

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 5.2 Recommended Operating Conditions

Symbol	Parameter				Conditions	Standard			Unit
						Min.	Typ.	Max.	
V_{CC}/AV_{CC}	Supply voltage					1.8	—	5.5	V
V_{SS}/AV_{SS}	Supply voltage					—	0	—	V
V_{IH}	Input “H” voltage	Other than CMOS input				0.8 Vcc	—	Vcc	V
		CMOS input	Input level switching function (I/O port)	Input level selection : 0.35 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0.5 Vcc	—	Vcc	V
					2.7 V ≤ Vcc < 4.0 V	0.55 Vcc	—	Vcc	V
					1.8 V ≤ Vcc < 2.7 V	0.65 Vcc	—	Vcc	V
				Input level selection : 0.5 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0.65 Vcc	—	Vcc	V
					2.7 V ≤ Vcc < 4.0 V	0.7 Vcc	—	Vcc	V
					1.8 V ≤ Vcc < 2.7 V	0.8 Vcc	—	Vcc	V
				Input level selection : 0.7 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0.85 Vcc	—	Vcc	V
					2.7 V ≤ Vcc < 4.0 V	0.85 Vcc	—	Vcc	V
					1.8 V ≤ Vcc < 2.7 V	0.85 Vcc	—	Vcc	V
		External clock input (XOUT)				1.2	—	Vcc	V
V_{IL}	Input “L” voltage	Other than CMOS input				0	—	0.2 Vcc	V
		CMOS input	Input level switching function (I/O port)	Input level selection : 0.35 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0	—	0.2 Vcc	V
					2.7 V ≤ Vcc < 4.0 V	0	—	0.2 Vcc	V
					1.8 V ≤ Vcc < 2.7 V	0	—	0.2 Vcc	V
				Input level selection : 0.5 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0	—	0.4 Vcc	V
					2.7 V ≤ Vcc < 4.0 V	0	—	0.3 Vcc	V
					1.8 V ≤ Vcc < 2.7 V	0	—	0.2 Vcc	V
				Input level selection : 0.7 Vcc	4.0 V ≤ Vcc ≤ 5.5 V	0	—	0.55 Vcc	V
					2.7 V ≤ Vcc < 4.0 V	0	—	0.45 Vcc	V
					1.8 V ≤ Vcc < 2.7 V	0	—	0.35 Vcc	V
		External clock input (XOUT)				0	—	0.4 Vcc	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH(peak)}$				—	—	−160	mA
$I_{OH(sum)}$	Average sum output “H” current	Sum of all pins $I_{OH(avg)}$				—	—	−80	mA
$I_{OH(peak)}$	Peak output “H” current	Drive capacity Low				—	—	−10	mA
		Drive capacity High				—	—	−40	mA
$I_{OH(avg)}$	Average output “H” current	Drive capacity Low				—	—	−5	mA
		Drive capacity High				—	—	−20	mA
$I_{OL(sum)}$	Peak sum output “L” current	Sum of all pins $I_{OL(peak)}$				—	—	160	mA
$I_{OL(sum)}$	Average sum output “L” current	Sum of all pins $I_{OL(avg)}$				—	—	80	mA
$I_{OL(peak)}$	Peak output “L” current	Drive capacity Low				—	—	10	mA
		Drive capacity High				—	—	40	mA
$I_{OL(avg)}$	Average output “L” current	Drive capacity Low				—	—	5	mA
		Drive capacity High				—	—	20	mA
$f_{(XIN)}$	XIN clock input oscillation frequency				2.7 V ≤ Vcc ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ Vcc < 2.7 V	—	—	5	MHz
fOCO40M	When used as the count source for timer RC (3)				2.7 V ≤ Vcc ≤ 5.5 V	32	—	40	MHz
fOCO-F	fOCO-F frequency				2.7 V ≤ Vcc ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ Vcc < 2.7 V	—	—	5	MHz
—	System clock frequency				2.7 V ≤ Vcc ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ Vcc < 2.7 V	—	—	5	MHz
$f_{(BCLK)}$	CPU clock frequency				2.7 V ≤ Vcc ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ Vcc < 2.7 V	—	—	5	MHz

Notes:
1. Vcc = 1.8 V to 5.5 V at Topr = −20°C to 85°C (N version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.
3. fOCO40M can be used as the count source for timer RC in the range of Vcc = 2.7 V to 5.5 V.

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance (2)		1,000 (3)	—	—	times
—	Byte program time		—	80	500	µs
—	Block erase time		—	0.3	—	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		—	—	5 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	µs
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly terminated until reading is enabled		—	—	30 + CPU clock × 1 cycle	µs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		0	—	60	°C
—	Data hold time (7)	Ambient temperature = 55°C	20	—	—	year

Notes:
1. Vcc = 2.7 V to 5.5 V at Topr = 0°C to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.5 Flash Memory (Data flash Block A to Block D) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance (2)		10,000 (3)	—	—	times
—	Byte program time (program/erase endurance ≤ 1,000 times)		—	160	1,500	µs
—	Byte program time (program/erase endurance > 1,000 times)		—	300	1,500	µs
—	Block erase time (program/erase endurance ≤ 1,000 times)		—	0.2	1	s
—	Block erase time (program/erase endurance > 1,000 times)		—	0.3	1	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		—	—	5 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	µs
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly terminated until reading is enabled		—	—	30 + CPU clock × 1 cycle	µs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		–20	—	85	°C
—	Data hold time (7)	Ambient temperature = 55°C	20	—	—	year

Notes:
1. Vcc = 2.7 V to 5.5 V at Topr = –20°C to 85°C (N version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

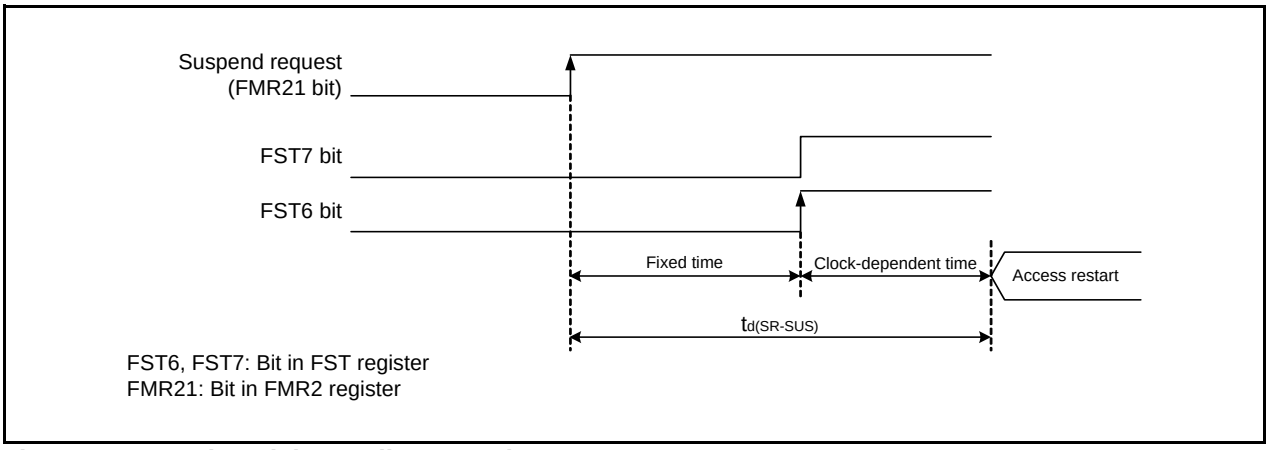


Figure 5.2 Time delay until Suspend

Table 5.10 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
—	High-speed on-chip oscillator frequency after reset	Vcc = 1.8 V to 5.5 V −20°C ≤ Topr ≤ 85°C	38.4	40	41.6	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register (2)	Vcc = 1.8 V to 5.5 V −20°C ≤ Topr ≤ 85°C	35.389	36.864	38.338	MHz
	High-speed on-chip oscillator frequency when the FRA6 register correction value is written into the FRA1 register and the FRA7 register correction value into the FRA3 register	Vcc = 1.8 V to 5.5 V −20°C ≤ Topr ≤ 85°C	30.72	32	33.28	MHz
—	Oscillation stability time	Vcc = 5.0 V, Topr = 25°C	—	0.5	3	ms
—	Self power consumption at oscillation	Vcc = 5.0 V, Topr = 25°C	—	400	—	μA

Notes:
1. Vcc = 1.8 V to 5.5 V, Topr = −20°C to 85°C (N version), unless otherwise specified.
2. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.11 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		60	125	250	kHz
—	Oscillation stability time	Vcc = 5.0 V, Topr = 25°C	—	30	100	μs
—	Self power consumption at oscillation	Vcc = 5.0 V, Topr = 25°C	—	2	—	μA

Note:
1. Vcc = 1.8 V to 5.5 V, Topr = −20°C to 85°C (N version), unless otherwise specified.

Table 5.12 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on (2)		—	—	2000	μs

Notes:
1. The measurement condition is Vcc = 1.8 V to 5.5 V and Topr = 25°C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.

Table 5.13 Electrical Characteristics (1) [4.2 V ≤ Vcc ≤ 5.5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High Vcc = 5 V	I_{OH} = –20 mA	Vcc – 2.0	—	Vcc	V
			Drive capacity Low Vcc = 5 V	I_{OH} = –5 mA	Vcc – 2.0	—	Vcc	V
		XOUT	Vcc = 5 V	I_{OH} = –200 μA	1.0	—	Vcc	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High Vcc = 5 V	I_{OL} = 20 mA	—	—	2.0	V
			Drive capacity Low Vcc = 5 V	I_{OL} = 5 mA	—	—	2.0	V
		XOUT	Vcc = 5 V	I_{OL} = 200 μA	—	—	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, KI0, KI1, KI2, KI3, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRCTRG, TRCCLK, $\overline{ADTRG}$, RXD0, RXD2, CLK0, CLK2, SCL2, SDA2			0.1	1.2	—	V
		$\overline{RESET}$			0.1	1.2	—	V
I_{IH}	Input “H” current		V_I = 5 V, Vcc = 5.0 V		—	—	5.0	μA
I_{IL}	Input “L” current		V_I = 0 V, Vcc = 5.0 V		—	—	–5.0	μA
R_{PULLUP}	Pull-up resistance		V_I = 0 V, Vcc = 5.0 V		25	50	100	kΩ
R_{fXIN}	Feedback resistance	XIN			—	0.3	—	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Note:
1. 4.2 V ≤ Vcc ≤ 5.5 V at Topr = –20°C to 85°C (N version), f(XIN) = 20 MHz, unless otherwise specified.

Table 5.14 Electrical Characteristics (2) [3.3 V ≤ Vcc ≤ 5.5 V]
(Topr = –20°C to 85°C (N version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 3.3 V to 5.5 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	6.5	15	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	5.3	12.5	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	3.6	—	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	3	—	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	2.2	—	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	1.5	—	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	—	7	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	3	—	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTTRD = MSTTRC = 1	—	1	—	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	—	90	400	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	15	100	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	4	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	3.5	—	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	2	5.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	5	—	µA

Table 5.17 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200	—	ns
$t_{W(CKH)}$	CLKi input “H” width	100	—	ns
$t_{W(CKL)}$	CLKi input “L” width	100	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	50	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	50	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

i = 0 to 2

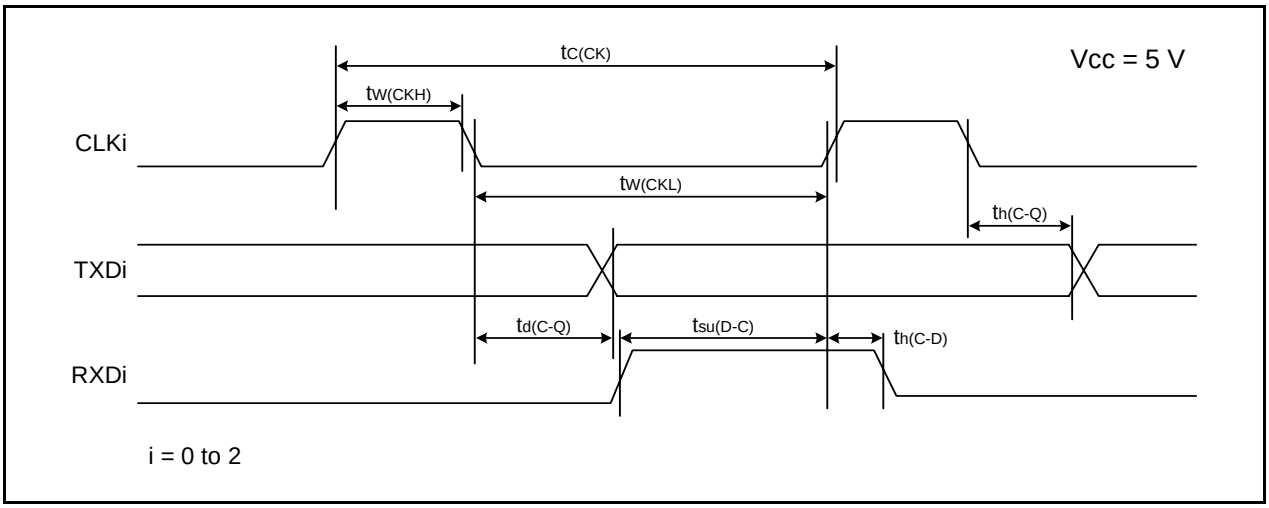


Figure 5.6 Serial Interface Timing Diagram when Vcc = 5 V

Table 5.18 External Interrupt $\overline{INTi}$ (i = 0 to 3) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	250 (1)	—	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	250 (2)	—	ns

Notes:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

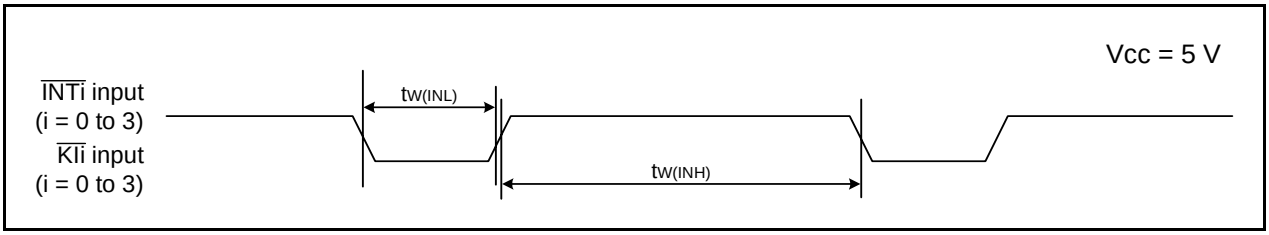


Figure 5.7 Input Timing for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{KIi}$ when Vcc = 5 V

Table 5.19 Electrical Characteristics (3) [2.7 V ≤ Vcc < 4.2 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High	I_{OH} = –5 mA	Vcc – 0.5	—	Vcc	V
			Drive capacity Low	I_{OH} = –1 mA	Vcc – 0.5	—	Vcc	V
		XOUT		I_{OH} = –200 μA	1.0	—	Vcc	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High	I_{OL} = 5 mA	—	—	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	—	—	0.5	V
		XOUT		I_{OL} = 200 μA	—	—	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, KI0, KI1, KI2, KI3, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRCTRG, TRCCLK, $\overline{ADTRG}$, RXD0, RXD2, CLK0, CLK2, SCL2, SDA2	Vcc = 3.0 V		0.1	0.4	—	V
		$\overline{RESET}$	Vcc = 3.0 V		0.1	0.5	—	V
I_{IH}	Input “H” current		V_I = 3 V, Vcc = 3.0 V		—	—	4.0	μA
I_{IL}	Input “L” current		V_I = 0 V, Vcc = 3.0 V		—	—	–4.0	μA
R_{PULLUP}	Pull-up resistance		V_I = 0 V, Vcc = 3.0 V		42	84	168	kΩ
R_{fXIN}	Feedback resistance	XIN			—	0.3	—	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Note:
1. 2.7 V ≤ Vcc < 4.2 V at Topr = –20°C to 85°C (N version), f(XIN) = 10 MHz, unless otherwise specified.

Timing requirements
(Unless Otherwise Specified: Vcc = 3 V, Vss = 0 V at Topr = 25°C)

Table 5.21 External Clock Input (XOUT)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XOUT)}$	XOUT input cycle time	50	—	ns
$t_{WH(XOUT)}$	XOUT input “H” width	24	—	ns
$t_{WL(XOUT)}$	XOUT input “L” width	24	—	ns

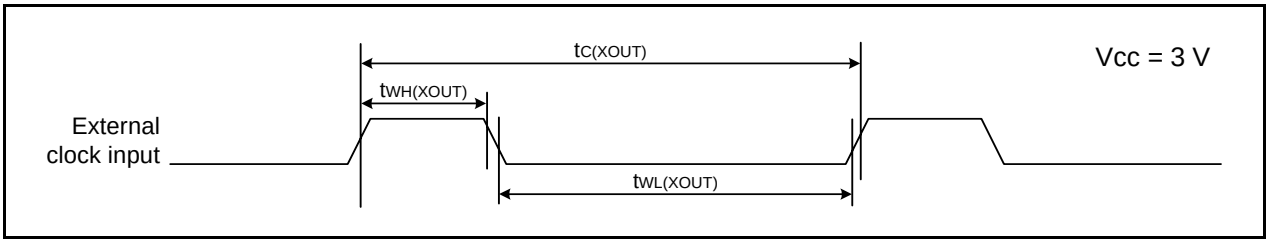


Figure 5.8 External Clock Input Timing Diagram when Vcc = 3 V

Table 5.22 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	300	—	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	120	—	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	120	—	ns

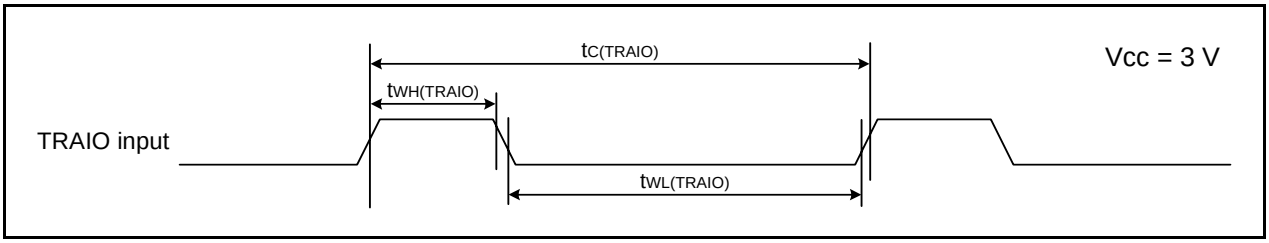


Figure 5.9 TRAIO Input Timing Diagram when Vcc = 3 V

Table 5.29 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	800	—	ns
$t_{W(CKH)}$	CLKi input “H” width	400	—	ns
$t_{W(CKL)}$	CLKi input “L” width	400	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	200	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	150	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

i = 0 to 2

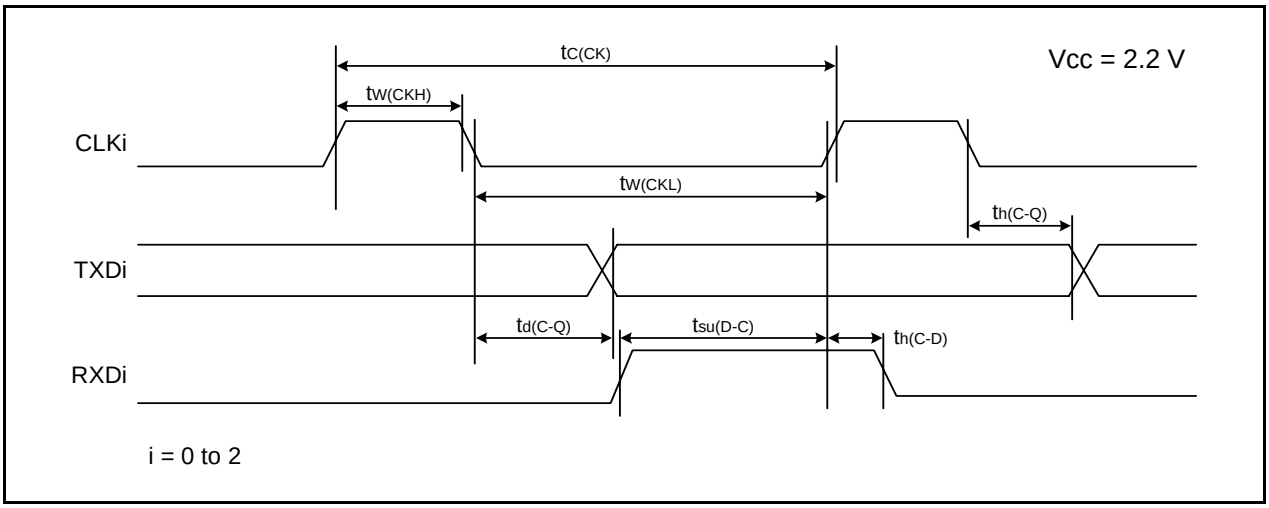


Figure 5.14 Serial Interface Timing Diagram when Vcc = 2.2 V

Table 5.30 External Interrupt $\overline{INTi}$ (i = 0 to 3) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	1000 (1)	—	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	1000 (2)	—	ns

Notes:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

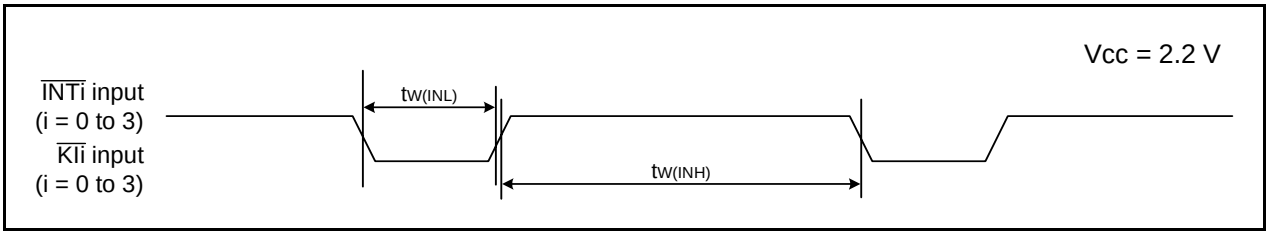
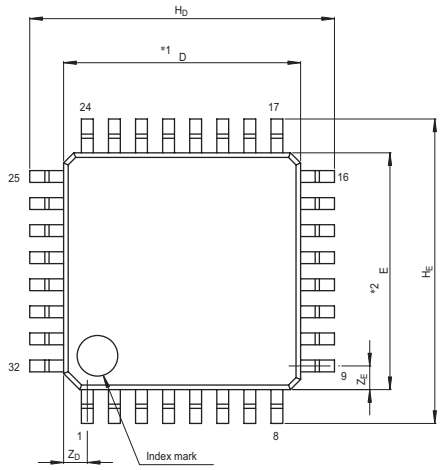


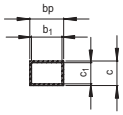
Figure 5.15 Input Timing for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{KIi}$ when Vcc = 2.2 V

Package Dimensions

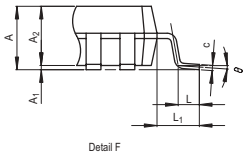
Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Electronics website.

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP32-7x7-0.80	PLQP0032GB-A	32P6U-A	0.2g





Terminal cross section



Detail F

NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.9	7.0	7.1
E	6.9	7.0	7.1
A_2	—	1.4	—
H_D	8.8	9.0	9.2
H_E	8.8	9.0	9.2
A	—	—	1.7
A_1	0	0.1	0.2
b_p	0.32	0.37	0.42
b_1	—	0.35	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.8	—
x	—	—	0.20
y	—	—	0.10
Z_D	—	0.7	—
Z_E	—	0.7	—
L	0.3	0.5	0.7
L_1	—	1.0	—

REVISION HISTORY	R8C/33T Group Datasheet

Rev.	Date	Description	
		Page	Summary
1.00	Mar 16, 2010	—	First Edition issued
1.10	Apr 26, 2011	All pages	“UART1” deleted
		3	Table 1.2 revised, Note 1 deleted
		4	Table 1.3, Note 1, Figure 1.1 revised
		5	Figure 1.2 revised
		6	Figure 1.3 revised
		7	Table 1.4 revised
		8	Table 1.5 revised
		12	3.1 “The internal ROM . . . with address 0FFFFh.” deleted
		14	Table 4.2 revised
		18	Table 4.6 revised
		19	Table 4.7 revised
		26	Table 5.1 revised
		27	Note 1 revised
		29	Table 5.3, Note 1 revised
		31	Table 5.5, Note 1, Note 7 revised, and Note 8 added
		32	Note 1 of Table 5.6 and Table 5.7 revised
		33	Note 1 of Table 5.8 and Table 5.9 revised
		34	Table 5.10, Note 1 of Table 5.10 and Table 5.11 revised
		35	Table 5.13, Note 1 revised
		36	Table 5.14 revised
		39	Table 5.19, Note 1 revised
		40	Table 5.20 revised
		43	Table 5.25, Note 1 revised
		44	Table 5.26 revised

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Renesas Electronics America Inc.
2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada
Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
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Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd.
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